

1-Line Uni-directional TVS Diode

Description

The PESDU1271P1 is an uni-directional TVS diode, to provide fast response time and ultra low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive data and power line. The PESDU1271P1 complies with the IEC 61000-4-2 (ESD) standard with ±30kV air and ±30kV contact discharge.

It is assembled into an ultra-small 1.0x0.6x0.5mm lead-free DFN package. The small size and high ESD protection make PESDU1271P1 an ideal choice to protect cell phone, digital cameras, audio players and many other portable applications.

Features

- Ultra small package: 1.0x0.6x0.5mm
- · Protects one data or power line
- Working voltage: 12 V
- Low clamping voltage
- · 2-pin leadless package
- Complies with following standards:

IEC 61000-4-2 (ESD) immunity test

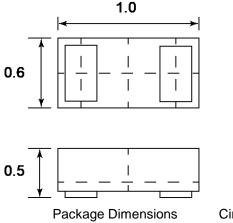
Air discharge: ±30kV

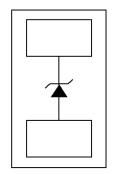
Contact discharge: ±30kV

IEC61000-4-5 (Lightning) 26A (8/20µs)

RoHS Compliant

Dimensions and Pin Configuration





Circuit and Pin Schematic

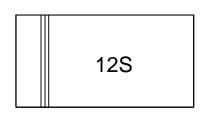
Mechanical Characteristics

- Package: DFN1006-2 (1.0×0.6×0.5mm)
- Case Material: "Green" Molding Compound.
- Moisture Sensitivity: Level 1 per J-STD-020
- · Marking Information: See Below

Applications

- Cellular Handsets & Accessories
- Personal Digital Assistants
- Notebooks & Handhelds
- Portable Instrumentation
- Digital Cameras

Marking Information



12S = Device Marking Code Bar denotes cathode

Ordering Information

Part Number	Shipping	Reel Size
PESDU1271P1	10000/Tape & Reel	7 inch



Absolute Maximum Ratings (TA=25°C unless otherwise specified)

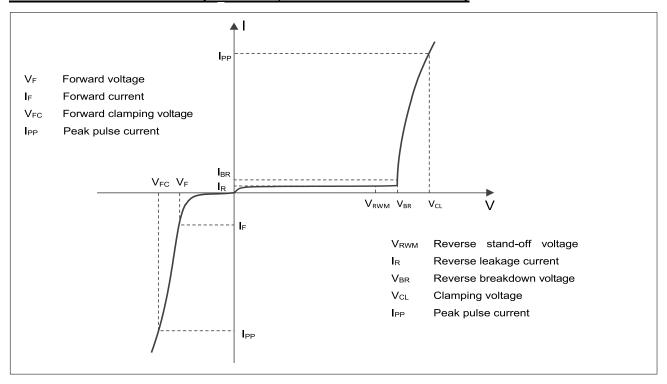
Parameter	Symbol	Value	Unit		
Peak Pulse Power (8/20μs)	Ppk	730	W		
Peak Pulse Current (8/20µs)	I _{PP}	26	Α		
ESD per IEC 61000-4-2 (Air)	V	±30	147		
ESD per IEC 61000-4-2 (Contact)	Vesd	±30	- kV		
Lead temperature	TL	260	°C		
Operating Temperature Range	Тор	-40 ~ + 85	°C		
Storage Temperature Range	T _{STG}	−55 ~ + 150	°C		

Electrical Characteristics (TA=25°C unless otherwise specified)

Parameter	Symbol	Min	Тур	Max	Unit	Test Condition
Reverse Working Voltage	V _{RWM}			12.0	V	Pin 1 to Pin 2
Breakdown Voltage	V_{BR}	13.0			V	$I_T = 1mA$
Reverse Leakage Current	I _R			1	μA	V _{RWM} = 12V
Clamping Voltage	Vc			28	V	I _{PP} =26A (8/20μs pulse),
Junction Capacitance	Сл		300		pF	V _R = 0V, f = 1MHz



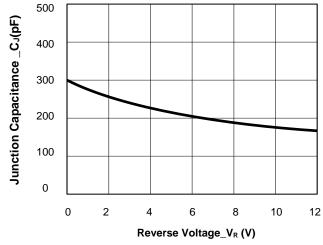
Electrical characteristics (T_A = 25℃, unless otherwise noted)

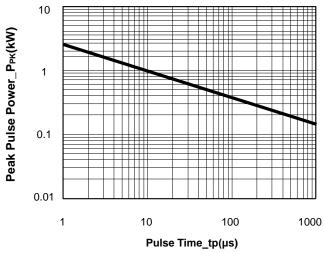


Definitions of electrical characteristics

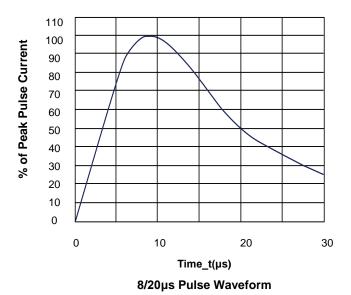


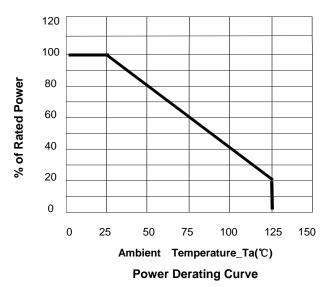
Typical Performance Characteristics (T_A=25°C unless otherwise Specified)





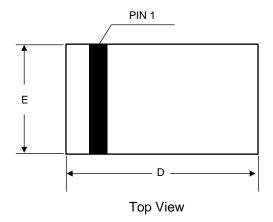
Junction Capacitance vs. Reverse Voltage Peak Pulse Power vs. Pulse Time

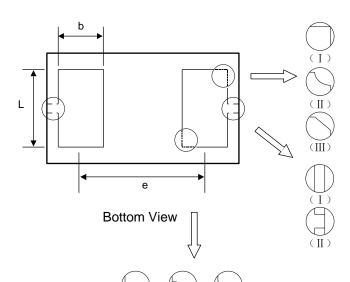


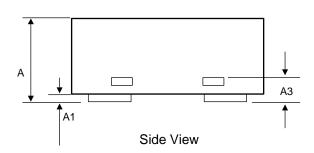




DFN1006-2 Package Outline Drawing

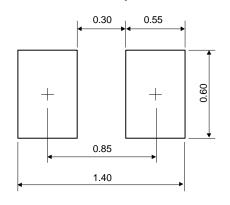






Symbol	ı	Dimensions in Millimeters			
	Min.	Тур.	Max.		
А	0.340	0.450	0.550		
A1	0.000	0.020	0.050		
A3		0.125 Ref.			
D	0.950	1.000	1.075		
E	0.490	0.600	0.675		
b	0.200	0.250	0.300		
L	0.450	0.500	0.550		
e		0.650 BSC			

Recommended PCB Layout (Unit: mm)

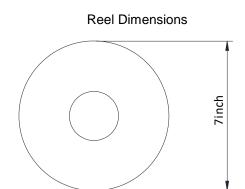


Notes:

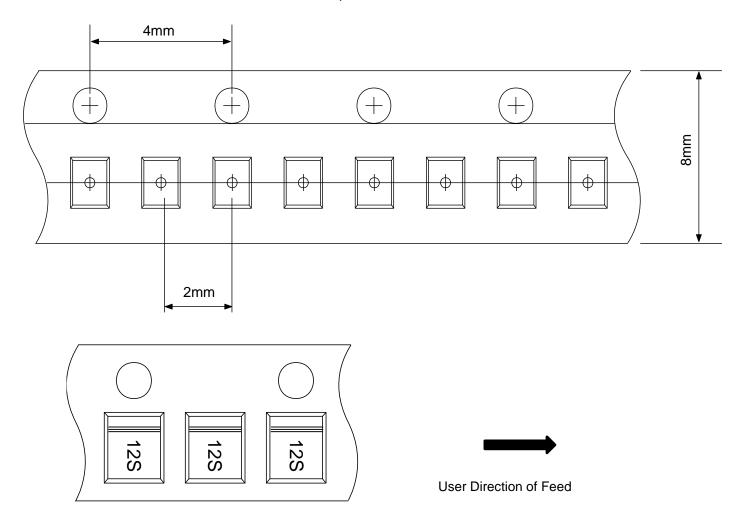
This recommended land pattern is for reference purposes only. Please consult your manufacturing group to ensure your PCB design guidelines are met.



TAPE AND REEL INFORMATION



Tape Dimensions





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